TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC573AP,TC74HC573AF,TC74HC573AFW

Octal D-Type Latch with 3-State Output

The TC74HC573A is a high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Its 8-bit D-type latche is controlled by a latch enable input (LE) and a output enable input ($\overline{\rm OE}$).

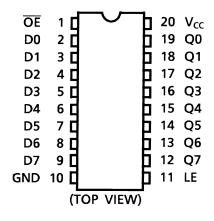
When the \overline{OE} input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

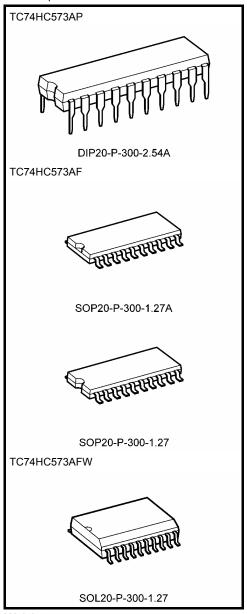
Features

- High speed: $t_{pd} = 13 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max)}$ at $T_a = 25 \text{°C}$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Output drive capability: 15 LSTTL loads
- Symmetrical output impedance: $|I_{OH}| = I_{OL} = 6 \text{ mA (min)}$
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2 to 6 V
- Pin and function compatible with 74LS573

Pin Assignment



Note: xxxFW (JEDEC SOP) is not available in Japan.



Weight

DIP20-P-300-2.54A : 1.30 g (typ.) SOP20-P-300-1.27A : 0.22 g (typ.) SOP20-P-300-1.27 : 0.22 g (typ.) SOL20-P-300-1.27 : 0.46 g (typ.)

IEC Logic Symbol

OE (1) LE (11)	EN C 1	
$ \begin{array}{c} D0 \\ \frac{(2)}{(3)} \\ D1 \\ \frac{(4)}{(4)} \\ D2 \\ \frac{(5)}{(5)} \\ D3 \\ \frac{(6)}{(7)} \\ D5 \\ \frac{(8)}{(9)} \\ D7 \\ \end{array} $	1D ▷ ▽	(19) Q0 (18) Q1 (17) Q2 (16) Q3 (15) Q4 (14) Q5 (13) Q6 (12) Q7

Truth Table

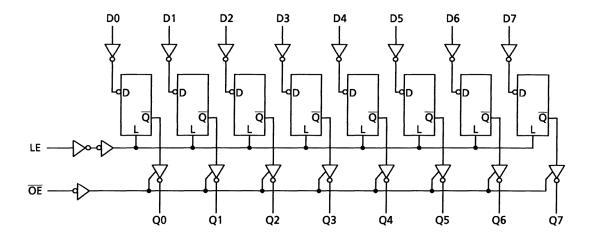
	Output		
ŌĒ	LE	D	Q
Н	Х	Х	HZ
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

HZ: High impedance

 $\mathsf{Q}_{\mathsf{n}} . \; \mathsf{Q}$ outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	–0.5 to 7	V
DC input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
DC output voltage	V _{OUT}	−0.5 to V _{CC} + 0.5	٧
Input diode current	I _{IK}	±20	mA
Output diode current	lok	±20	mA
DC output current	lout	±35	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	–65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of Ta = -40 to $65^{\circ}C$. From Ta = 65 to $85^{\circ}C$ a derating factor of -10 mW/°C shall be applied until 300 mW.

Recommended Operating Conditions (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2 to 6	V
Input voltage	V _{IN}	0 to V _{CC}	V
Output voltage	V _{OUT}	0 to V _{CC}	٧
Operating temperature	T _{opr}	−40 to 85	°C
		0 to 1000 (V _{CC} = 2.0 V)	
Input rise and fall time	t _r , t _f	0 to 500 (V _{CC} = 4.5 V)	ns
		0 to 400 (V _{CC} = 6.0 V)	

Note: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

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Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Symbol Test Condition			Ta = 25°C			Ta –40 to	Unit	
	- J			V _{CC} (V)	Min	Тур.	Max	Min	Max	
				2.0	1.50	_	_	1.50	_	
High-level input voltage	V _{IH}		_	4.5	3.15	_	_	3.15	_	V
ŭ				6.0	4.20	—	_	4.20	_	
				2.0	_		0.50	_	0.50	
Low-level input voltage	V _{IL}		_	4.5	_		1.35	_	1.35	V
Ğ				6.0	_	_	1.80	_	1.80	
				2.0	1.9	2.0	_	1.9	_	
	output V _{OH}		$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	
High-level output voltage		V _{IN} = V _{IH} or V _{IL}		6.0	5.9	6.0	_	5.9		V
			$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	
			$I_{OH} = -7.8 \text{ mA}$	6.0	5.68	5.80	_	5.63	_	
				2.0	_	0.0	0.1	_	0.1	
	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	
Low-level output voltage				6.0		0.0	0.1	_	0.1	V
			I _{OL} = 6 mA	4.5	_	0.17	0.26	_	0.33	
			I _{OL} = 7.8 mA	6.0		0.18	0.26	_	0.33	
3-state output off-state current	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		6.0	_	_	±0.5	_	±5.0	μА
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0	_	_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	V _{IN} = V _{CC} or	r GND	6.0	_	_	4.0	_	40.0	μА

Timing Requirements (input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition	Test Condition				Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width			2.0	_	75	95	
	t _{W (H)}	_	4.5	_	15	19	ns
(LE)			6.0	_	13	16	
Minimum oot un timo			2.0	_	50	65	
Minimum set-up time	ts	_	4.5	_	10	13	ns
(data)			6.0	_	9	11	
Minimum hold time			2.0	_	5	5	
	t _h	_	4.5	_	5	5	ns
(data)			6.0	_	5	5	

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AC Characteristics (input: $t_r = t_f = 6$ ns)

Characteristics Symbo		Test Co	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
5.1.a.1 d 51.51.51.51	Cy20.		CL (pF)	V _{CC} (V)	Min	Тур.	Max	Min	Max	J
	t _{TLH}			2.0	_	20	60	_	75	
Output transition time	t _{THL}	_	50	4.5	_	6	12	_	15	ns
	THL			6.0	_	5	10	_	13	
				2.0	_	50	115	_	145	
			50	4.5	_	15	23	_	29	
Propagation delay time	t_{pLH}			6.0	_	13	20	_	25	ns
(LE-Q)	t_{pHL}			2.0	_	60	155	_	195	113
			150	4.5	_	20	31	_	39	
				6.0	_	17	26	_	33	
				2.0		42	110	_	140	
			50	4.5	_	14	22	_	28	
Propagation delay time	t_{pLH}			6.0	_	12	19	_	24	ns
(D-Q)	t_{pHL}	_		2.0	_	57	150	_	190	115
,			150	4.5	_	19	30	_	38	
				6.0	_	16	26	_	32	
				2.0	_	55	140	_	175	
			50	4.5	_	17	28	_	35	
Output enable time	t_{pZL}	$R_L = 1 k\Omega$		6.0	_	14	24	_	30	20
Output eriable time	t _{pZH}	K[= 1 K22		2.0	_	66	180	_	225	ns
			150	4.5	_	22	36	_	45	
				6.0	_	19	31	_	38	
	4 .			2.0	_	40	125	_	155	
Output disable time	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	50	4.5	_	17	25	_	31	ns
	t _{pHZ}			6.0	_	15	21	_	26	
Input capacitance	C _{IN}	_		_	5	10	_	10	pF	
Output capacitance	C _{OUT}	_	_		_	10	_	_	_	pF
Power dissipation	C _{PD}					5 1				pF
capacitance	(Note)	_				51				þΓ

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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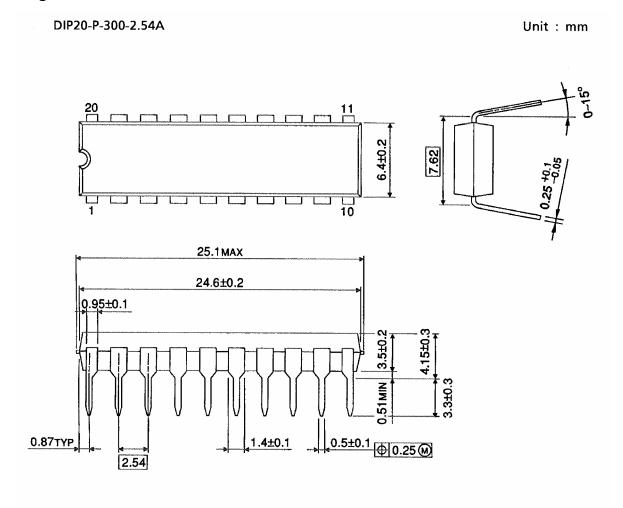
Average operating current can be obtained by the equation:

$$I_{CC} (opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per \ latch)$$

And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

$$C_{PD}$$
 (total) = 33 + 18 · n

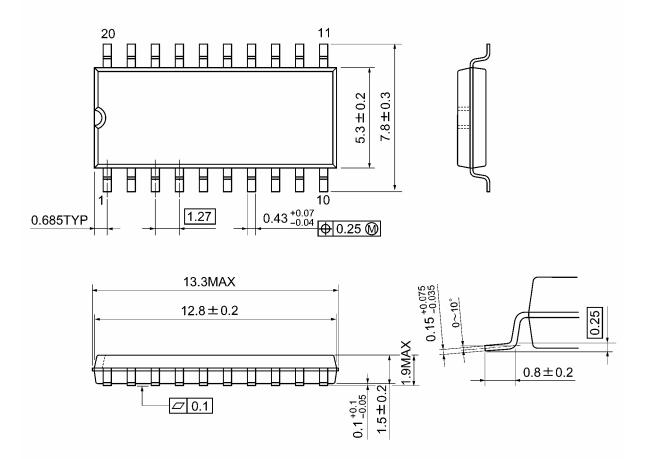
Package Dimensions



Weight: 1.30 g (typ.)

Package Dimensions

SOP20-P-300-1.27A Unit: mm



Weight: 0.22 g (typ.)



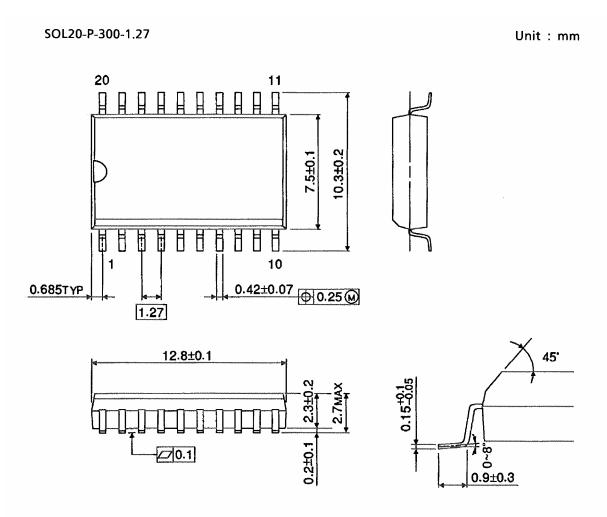
Package Dimensions

SOP20-P-300-1.27 Unit: mm 20 11 5.3±0.2 7.8±0.3 (300mil) 7.62 B 10 0.43±0.1 0.25 M 0.685TYP 1.27 13.3MAX 12.8±0.2 **2**0.1 0.8±0.2

Weight: 0.22 g (typ.)



Package Dimensions (Note)



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Note: This package is not available in Japan.

Weight: 0.46 g (typ.)

Note: Lead (Pb)-Free Packages

DIP20-P-300-2.54A SOP20-P-300-1.27A

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